



AU40N120T1

1200V /40A Trench Field Stop IGBT

FEATURES

- High breakdown voltage to 1200V for improved reliability
- Trench-Stop Technology offering :
 - very tight parameter distribution
 - high ruggedness, temperature stable behavior
 - Short circuit withstand time – 10 μ s
 - High ruggedness, temperature stable
 - LOW $V_{CE(SAT)}$
 - Easy parallel switching capability due to positive temperature coefficient in $V_{CE(SAT)}$
- Enhanced avalanche capability

APPLICATION

- Frequency Converters
- Motor Drive
- Specified application conditions

AU40N120T1	TO247	Tube
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Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-Emitter Breakdown Voltage	V_{CE}	1200	V
DC collector current, limited by T_{jmax} $T_C = 25^\circ C$ $T_C = 100^\circ C$	I_C	80 40	A
Continuous Gate-emitter voltage	V_{GE}	± 20	V
Transient Gate-emitter voltage	V_{GE}	± 30	V
Turn off safe operating area $V_{CE} = 1200V$, $T_j = 150^\circ C$	-	160	A
Pulsed Collector Current, $V_{GE} = 15V$, t_p limited by T_{jmax}	I_{CM}	160	A
Short Circuit Withstand Time, $V_{GE} = 15V$, $V_{CE} = 600V$	T_{sc}	10	μs
Power dissipation, $T_j = 25^\circ C$	P_{tot}	416	W
Operating junction temperature	T_j	-40...+150	$^\circ C$
Storage temperature	T_s	-55...+150	$^\circ C$
Soldering temperature, wave soldering 1.6mm (0.063in.) from case for 10s	-	260	$^\circ C$

Thermal Resistance

Parameter	Symbol	Max. Value	Unit
IGBT thermal resistance, junction - case	$R(j-c)$	0.3	K/W
Diode thermal resistance, junction - case	$R(j-c)$	0.6	K/W
Thermal resistance, junction - ambient	$R(j-a)$	40	K/W

Electrical Characteristics of the IGBT ($T_j = 25^\circ\text{C}$ unless otherwise specified) :

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Static						
Collector-Emitter breakdown voltage	BV_{CES}	$V_{GE}=0V, I_C=250\mu A$	1200	1300	-	V
Gate threshold voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C=250\mu A$	5.1	5.8	6.4	V

Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Dynamic , at $T_j = 25^\circ \text{C}$						
Turn-on delay time	$t_{d(on)}$	$V_{CC} = 600\text{V}$, $I_C = 40\text{A}$, $V_{GE} = 0/15\text{V}$, $R_g = 12\Omega$	-	55	-	ns
Rise time	t_r		-	20	-	ns
Turn-on energy	E_{on}		-	2.4	-	mJ
Turn-off delay time	$t_{d(off)}$		-	230	-	ns
Fall time	t_f		-	100	-	ns
Turn-off energy	E_{off}		-	1.5	-	mJ

Fig. 1 FBSOA characteristics

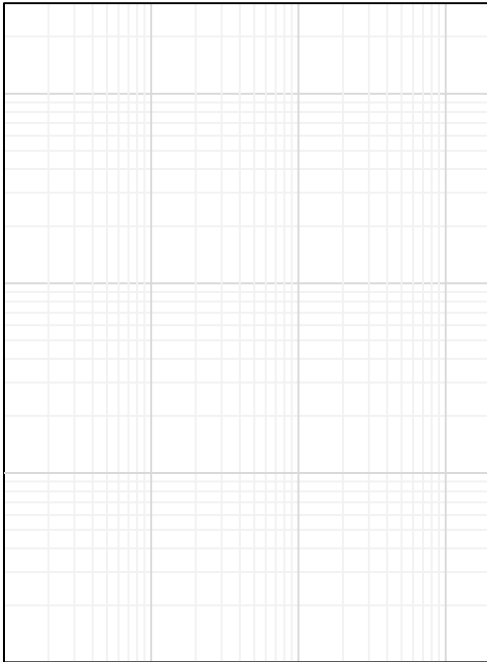


Fig. 2 Load Current vs. Frequency

Fig. 3 Power dissipation as a function of T_C

Fig. 4 Short circuit time and current vs. V_{GE}

Fig. 5 Output characteristics

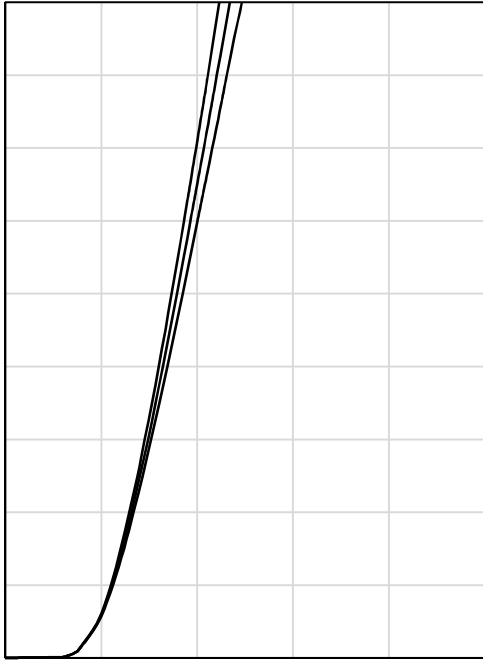


Fig. 6 Saturation voltage characteristics

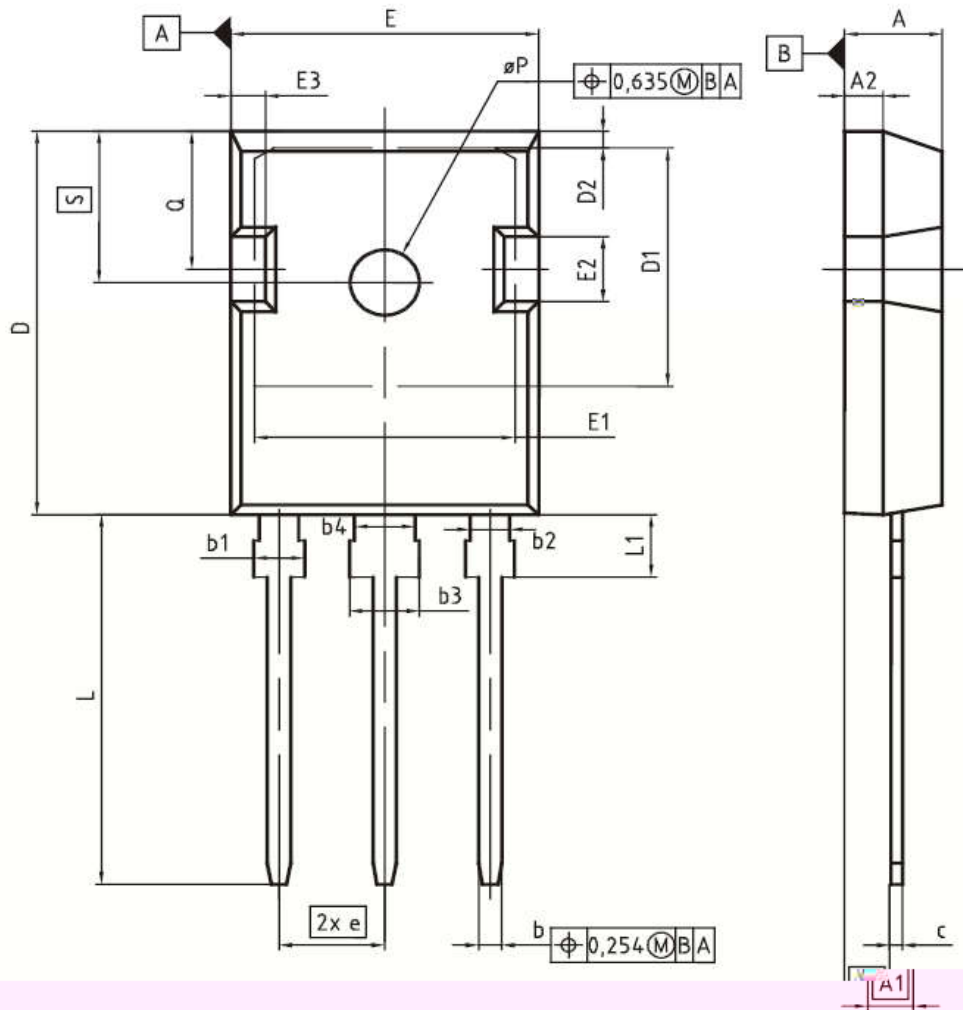
Fig. 7 Switching times vs. gate resistor

Fig. 8 Switching times vs. collector current

600V

600V

PG-TO247-3



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.53	5.21	0.190	0.205
A1	2.27	2.54	0.089	0.100
A2	1.85	2.16	0.073	0.085
b	1.07	1.33	0.042	0.052
b1	1.90	2.41	0.075	0.095
b2	1.90	2.16	0.075	0.085
b3	2.87	3.38	0.113	0.133
b4	2.87	3.13	0.113	0.123
c	0.55	0.68	0.022	0.027
D	20.80	21.10	0.819	0.831
D1	16.25	17.65	0.640	0.695
D2	0.95	1.35	0.037	0.053
E	15.70	16.13	0.618	0.635
E1	13.10	14.15	0.516	0.557
E2	3.68	5.10	0.145	0.201
E3	1.00	2.60	0.039	0.102
e	5.44 (BSC)		0.214 (BSC)	
N	3		3	
L	19.80	20.32	0.780	0.800
L1	4.10	4.47	0.161	0.176
eP	3.50	3.70	0.138	0.146
Q	5.49	6.00	0.216	0.236
S	6.04	6.30	0.238	0.248